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Attorney's Docket No.: 5308-291

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Sheppard et al.
Application No.: 10/758,871
Filed: January 16, 2004
For: **NITRIDE-BASED TRANSISTORS WITH A PROTECTIVE LAYER AND A LOW-DAMAGE RECESS AND METHODS OF FABRICATION THEREOF**

Confirmation No.: 6572
Group Art Unit: 2815
Examiner: N. Drew Richards

Date: June 8, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449 together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the amendment by the U.S. Patent and Trademark Office to 37 C.F.R. § 1.98(a)(2)(ii) effective October 21, 2004. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Therefore, no fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

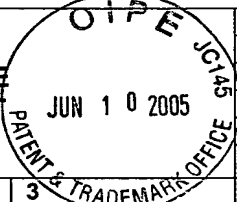
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Erin A. Campion

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| Substitute form 1449A/PTO | |  | | Complete if Known | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | Application Number | 10/758,871 | | |
| | | Filing Date | January 16, 2004 | | |
| | | First Named Inventor | Sheppard et al. | | |
| | | Group Art Unit | 2815 | | |
| | | Examiner Name | Richards, N. Drew | | |
| Sheet | 1 | of | 3 | Attorney Docket Number | 5308-291 |

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